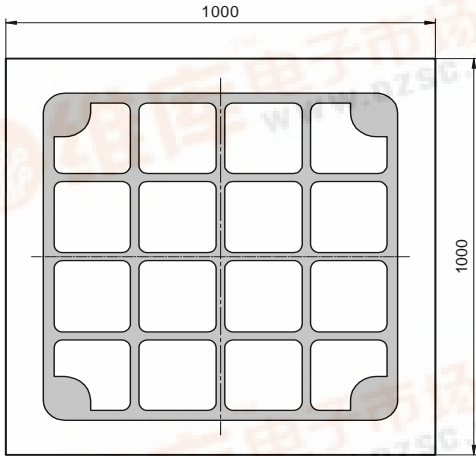


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	N (cathode) up

	typ. dimensions (μm)
	<u>typ. thickness</u> 160 (± 25) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 0.5 μm structured, 25% covered

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.3	1.5	V
Forward voltage ¹	$I_F = 350 \text{ mA}$	V_F		1.5	1.8	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	3.5	5		mW
Radiant power ¹	$I_F = 350 \text{ mA}$	Φ_e	70	90		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_P	860	870	880	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		35		nm
Switching time	$I_F = 20 \text{ mA}$	t_r, t_f		20		ns

¹Measured on bare chip glued on a $\varnothing 8 \times 1 \text{ mm}$ Cu header with *EPIGAP* equipment

Labeling

Type	Lot	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	$\lambda_P(\text{typ})$ [nm]	Quantity
ELC-870-21					

Packing: Chips on adhesive film with wire-bond side on top

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each application by the customer themselves.

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